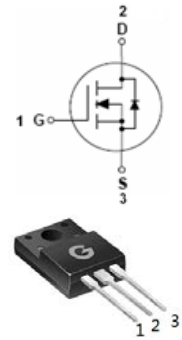


### Features

- $R_{DS(ON)}=1.35\Omega@V_{GS} = 10V$ .
- Ultra Low Gate Charge (Typical 30nC ).
- Low Reverse Transfer Capacitance.  
(  $C_{RSS} = \text{Typical } 18 \text{ pF}$  )
- Fast Switching Capability.
- Avalanche Energy Specified.
- Improved dv/dt Capability, High Ruggedness.



BLR7N65F

ITO-220AB

### Mechanical Data

- Case: ITO-220AB.
- Molding Compound, UL Flammability Classification Rating 94V-0.
- Terminals: Matte Tin Plated Leads, Solderable Per MIL-STD-202, Method 208.

### Ordering Information

Part Number	Package	Shipping	Marking Code
BLR7N65F□	ITO-220AB	50/Tube	R7N65F

□: none is for Lead Free package;

“G” is for Halogen Free package.

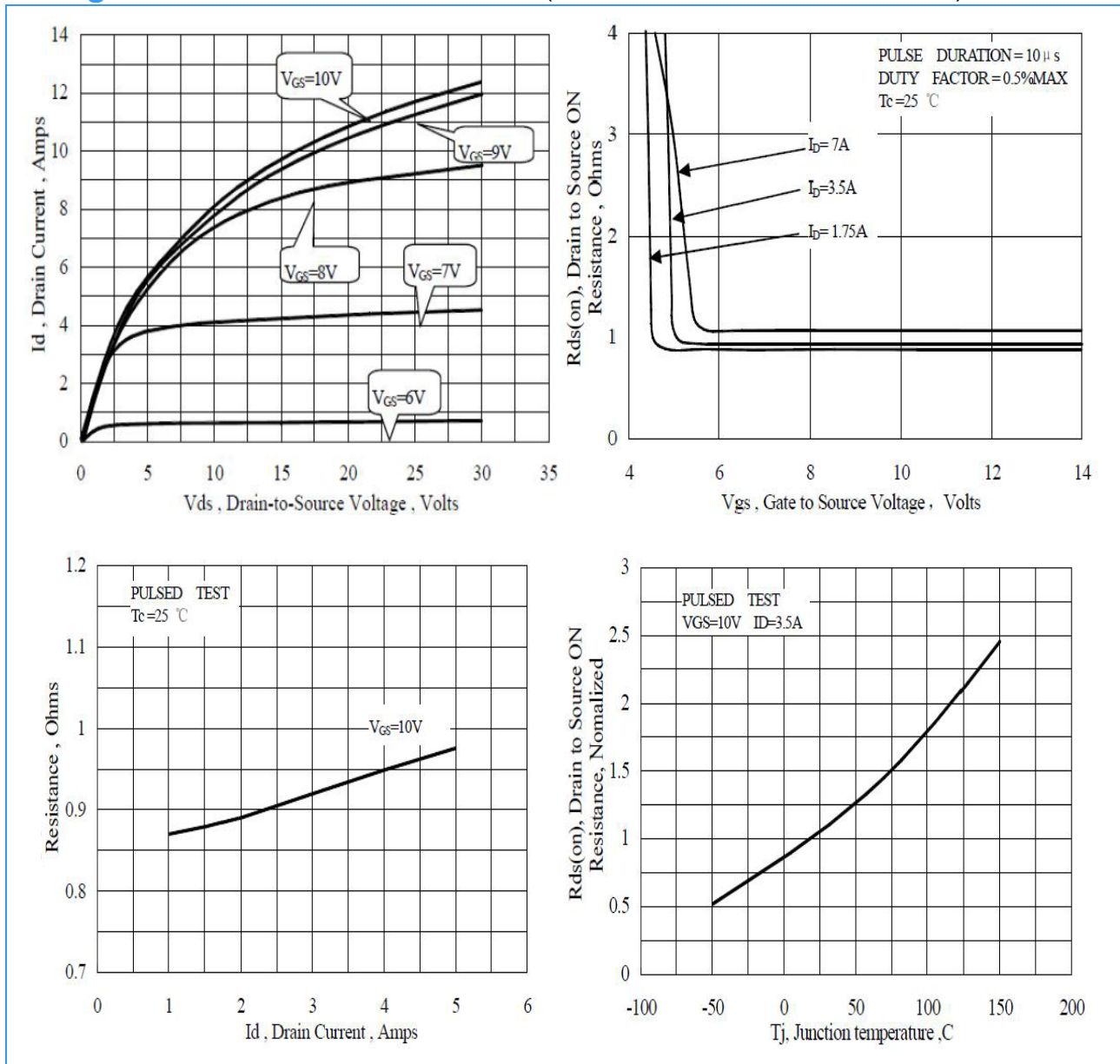
### Maximum Ratings (@ $T_A=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain-Source Voltage	650	V
$V_{GSS}$	Gate -Source Voltage	$\pm 30$	V
$I_D$	Continuous Drain Current	7	A
$I_{DM}$	Pulsed Drain Current	28	A
$E_{AS}$	Single Pulse Avalanche Energy	450	mJ
$P_D$	Power Dissipation	2.5	W
$T_J$	Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics (@ $T_A=25^\circ\text{C}$ unless otherwise specified)

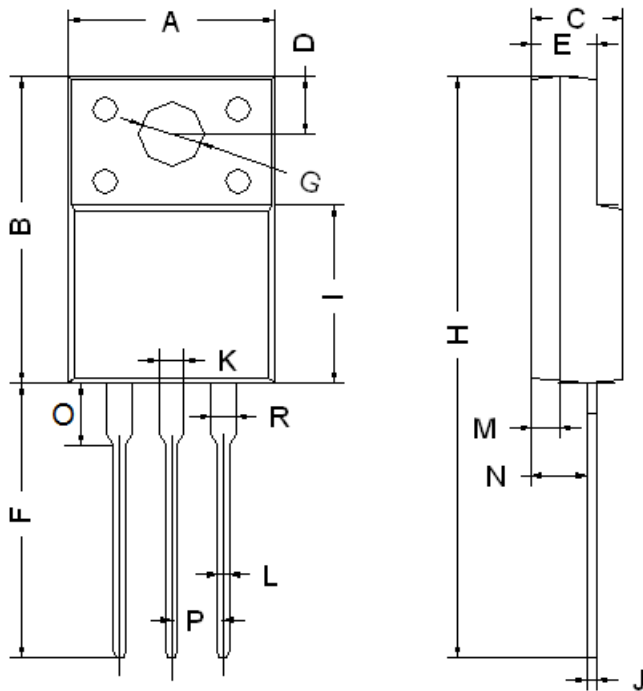
Symbol	Parameter	Test conditions	MIN	TYP	MAX	UNIT
<b>OFF Characteristics</b>						
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	-	-	V
$I_{DSS}$	Drain to Source Leakage Current	$V_{DS}=650V, V_{GS}=0V$	-	-	1	$\mu A$
$I_{GSS}$	Gate-body Leakage	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	$\pm 100$	$\mu A$
<b>ON Characteristics</b>						
$R_{DS(ON)}$	Static Drain-Source On-resistance	$V_{GS}=10V, I_D=3.5A$	-	-	1.4	$\Omega$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	1123	-	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	110	-	
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	11	-	

### Ratings and Characteristic Curves ( $T_A=25^\circ\text{C}$ unless otherwise noted)



Package Outline Dimensions(unit:mm)

ITO-220AB



ITO-220AB		
Dim	Min	Max
A	9.90	10.30
B	14.80	15.20
C	4.30	4.70
D	2.50	2.90
E	2.80	3.30
F	13.00	13.60
G	3.10	3.30
H	28.00	28.60
I	7.90	8.90
J	0.40	0.60
L	0.70	0.90
M	1.30	1.50
N	2.60	2.80
O	2.60	3.10
P	2.45	2.65
K/R	1.10	1.30

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